EAST - [10605402.wsp=1]

File View Edit Tools Window Help

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  - L1: (445) ("shallow trench" or "shallow-trench") with (dopant) with (region or area))
  - L2: (11162) STI
  - L3: (291) 1 and 2
  - L4: (91512) "438"/$T.ccls.
  - L5: (182) 3 and 4
  - L6: (3526909) @pd<"20011105"
  - L7: (106) 5 and 6
  - L8: (93017) patterned with (mask or PR)
  - L9: (55) 7 and 8
  - L10: (6132) trench with capacitor
  - L11: (14) 9 and 10
  - L12: (41) 9 not 11
  - L13: (653652) ion ir implant$
  - L14: (56[9]14) ion or implant$
  - L15: (14) 11 and 14
  - L16: (4838) "channel stop" or "channel-stop"
  - L17: (0) 15 and 16
  - L18: (3) 9 and 16
  - L19: (3789247) thickness or thick or A. or angstroms or meters
  - L20: (19) 11 and 19
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	O	?	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval Clas	Inventor	S	C	P			
1			US 20020123198 A1	20020905	8	Method of fabricating a self-aligned shallow trench isolation	438/296	257/501; 257/503;		Lee, Chia-Te						
2			US 20020066917 A1	20020606	27	DRAM with vertical transistor and trench capacitor memory cells and met	257/301	257/296; 257/E21.653;		Jagpraksh, Venkatachalam C. et al.						
3			US 6514816 B2	20030204	8	Method of fabricating a self-aligned shallow trench isolation	438/248	257/E21.549; 257/E21.651;		Lee, Chia-Te						

Ready